

CORRECTION

[View Article Online](#)
[View Journal](#) | [View Issue](#)



Cite this: *J. Mater. Chem. C*, 2022, **10**, 11811

Correction: Composition control of conformal crystalline GeSbTe films by atomic layer deposition supercycles and tellurization annealing

Yewon Kim,^a Kwonyoung Kim,^a Okhyeon Kim,^a Chang Yup Park,^b Dong Geon Koo,^b Dong-Ho Ahn,^b Bong Jin Kuh^b and Won-Jun Lee^{*a}

DOI: 10.1039/d2tc90156k

rsc.li/materials-c

Correction for 'Composition control of conformal crystalline GeSbTe films by atomic layer deposition supercycles and tellurization annealing' by Yewon Kim *et al.*, *J. Mater. Chem. C*, 2022, **10**, 9691–9698, DOI: <https://doi.org/10.1039/D2TC00784C>.

The authors regret errors in affiliation *b* of the coauthors in the published article, from which the words “Samsung Electronics Co., Ltd.” were unfortunately omitted. The correct affiliation list is as shown here.

The Royal Society of Chemistry apologises for these errors and any consequent inconvenience to authors and readers.

^a Departments of Nanotechnology and Advanced Materials Engineering, Sejong University, Seoul 05006, Republic of Korea. E-mail: wjlee@sejong.ac.kr

^b Process Development, Semiconductor R&D Center, Samsung Electronics Co., Ltd., 1, Samsungjeonja-ro, Hwaseong-si, Gyeonggi-do 18448, Republic of Korea

